

EAS [Untitled]:1

File View Edit Tools Window Help

Drafts

ISNR

Pending

Active

L2: (534) (257/376,385,492,493).CCLS

L3: (117) dop\$3 near3 buried adj layer with dop\$3 near3 epitaxial near3 layer

L4: (4) 3 and lattice near3 match\$3

L5: (2) 3 and (concentration profile gradient) and lattice with match\$3

L6: (31) 3 and dopant near3 (concentration profile gradient)

L7: (38) 3 and dopant near3 (concentration profile gradient)

L8: (6) 7 and lattice

L9: (2) ("4378259").PN

L10: (158) (438/491,495,499).CCLS

L11: (2) 3 and 10

L12: (1) 2 and 10

Failed

Saved

DBs

USPAT,US-PGPUB,EPO,JPO,DEFT,Others

Default operator: DR

Highlight all hit terms initially

2 and 10

Assign New Assignments Group Print View Title

	U	I	Document ID	Issue Date	Pages	Title	Current	Cur Re	Inventor	S	C	P	2	3	4	5
1	r	r	US 4247862 A	19810127	11	Ionization resistant MOS	257/297	148/	Klein, Raphael	r	r	r	r	r	r	r

File Command Window

Ready

NUM